#### A report on

# Custom Layout and Schematic Design of a Multi-fingered CMOS inverter for driving a load capacitance of 1pF

By

Akshit Goel 2016A3PS0317P Saksham Consul 2016A8PS0424P Nishad Sahu 2016A3PS0215P

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EEE F313/ INSTRF313 - Analog & Digital VLSI Design

Under the Guidance of

Prof. Anu Gupta
Instructor In-charge *EEE F313/ INSTR F313*EEE Department, BITS Pilani, Pilani Campus



Birla Institute of Technology and Science, Pilani

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## 1. Problem Statement and Interpretation

Design a CMOS Inverter at 500MHz with load capacitance of 10pF.

- (a)Plot the energy and delay graph.
- (b)Plot the short circuit and switching power graph.

Model File – tsmc018 (180nm technology)

**Supply voltage** − 1.8 V

## Interpretation -

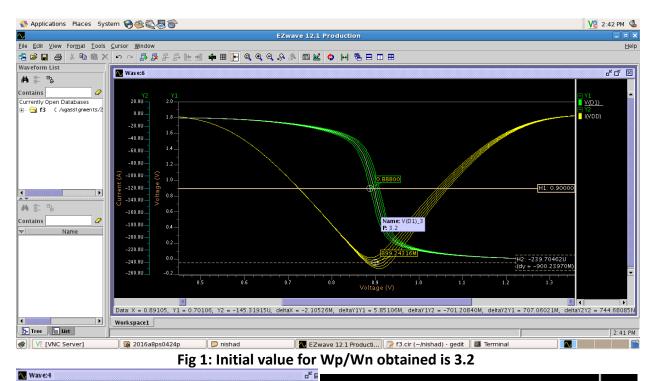
CMOS inverter is the best topology for achieving high voltage swing and minimum delay because of the combination of complementary Pull up and Pull down network. This is why it is one of the most used topology in ICs all over the world. The specification of the inverter given in the question has high frequency as well as a high capacitive load. Initial pen-paper calculations and simulation have yielded a (W/L)p ratio of around 600 using 180 nm technology. So, as it will lead to around 30 fingers which can be cumbersome for the layout, in consultation with course IC Prof. Anu Gupta we decided to work with 1pF capacitor load.

## 2. Calculation of design parameters

a. Approximation of Wp/Wn for equal drive capability

## **Concept Used:**

- Maximum drive current is at threshold switching voltage which is at Vdd/2 for a CMOS with equal drive capability
- T<sub>PHL</sub> = T<sub>PLH</sub> at equal drive capability



V(51)

| V(51) | 2.0 | 1.8 | 1.5 | 1.5 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1.0 | 1

H1: 0.90253

H1: 0.90253

Fig 2: Delay analysis using Wp/Wn =3.2 , (W/L)n=50

V(G1)

V(D1)

## From figure 1

 $T_{PHL} = 0.19 \text{ ns (NMOS 'ON')}$ 

 $T_{PLH} = 0.15 \text{ ns (PMOS 'ON')}$ 

So, the drive capability of NMOS is less so we need to increase Wn, keeping Wp same. Our final aim is to achieve delay = 0.15 ns which is 7.5 % of the time period, so we increase Wn to 10800N i.e (W/L)n=60.

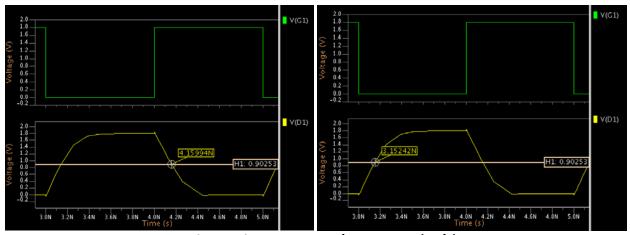


Fig 3: Delay analysis using Wp/Wn =2.67, (W/L)n=60

## From figure 3

 $T_{PHL} = 0.16 \text{ ns (NMOS 'ON')}$ 

 $T_{PLH} = 0.15 \text{ ns (PMOS 'ON')}$ 

So, the drive capability of NMOS is still slightly less. So we need to increase Wn and decrease Wp in order to avoid large diffusion area size.

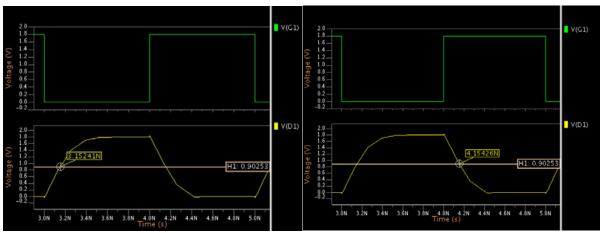


Fig 4: Delay analysis using Wp/Wn =2.42, (W/L)n=62

From figure 4

 $T_{PHL} = 0.15 \text{ ns (NMOS 'ON')}$ 

 $T_{PLH} = 0.15 \text{ ns (PMOS 'ON')}$ 

So, the drive capability of NMOS and PMOS are equal. Hence, these are the values which will be used in making the layout.

L=180nm

Wn=62 x 180 nm = 11,160 nm

 $Wp = 2.42 \times 11,160 = 27000 \text{ nm (approx)}$ 

## 3. Custom Layout Design

a. Layout

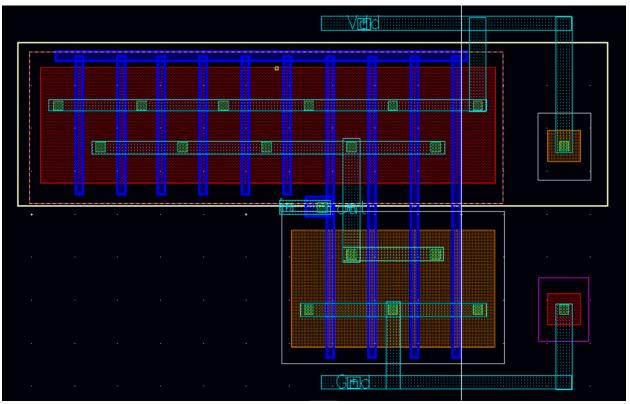


Fig 5: Multi-Fingered Layout using 4 Metal File in Virtuoso Cadence

PMOS has 10 fingers each having W/L = 2700/180 = 15

So, 
$$(W/L)p = 150$$

NMOS has 4 fingers each having W/L = 2790/180 = 15.5

So, 
$$(W/L)n = 62$$

Hence, Wp/Wn = 2.42

#### b. DRC

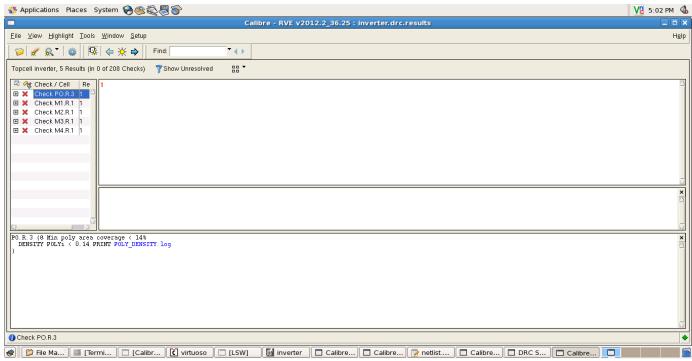


Fig 6: Running Design Rules Check (DRC) using Calibre

DRC was passed successfully (i.e all errors except density errors were removed) and at the same time, care was taken to ensure minimum area to decrease parasitics. Result of this can be seen in PEX section were we obtained output capacitance due to parasitics in Femto Farads in spite of having a multi-fingered layout which occupies large area.

#### c. LVS

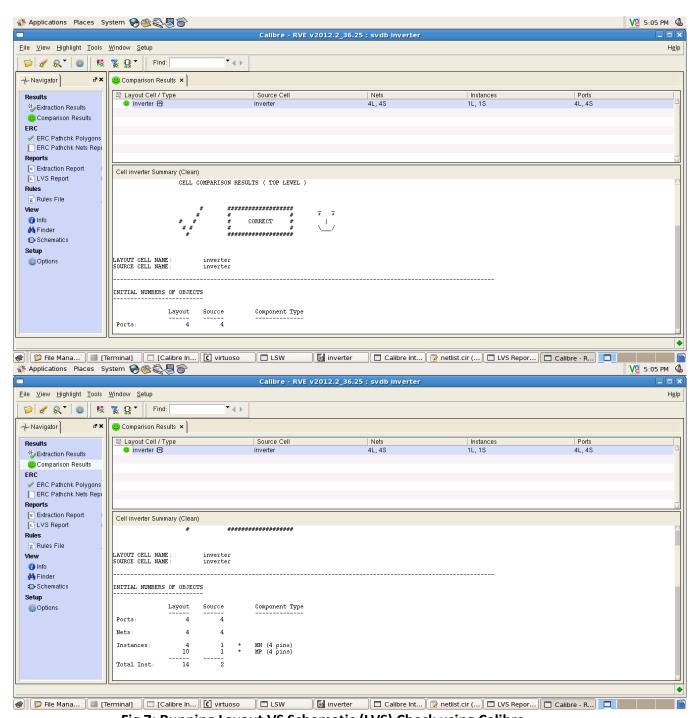


Fig 7: Running Layout VS Schematic (LVS) Check using Calibre

# Schematic used for LVS -

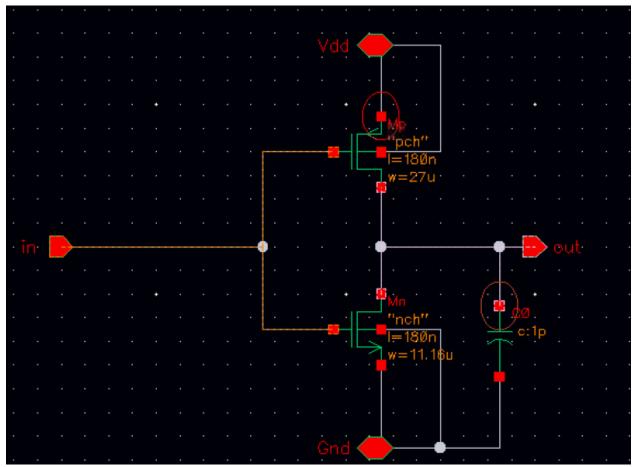


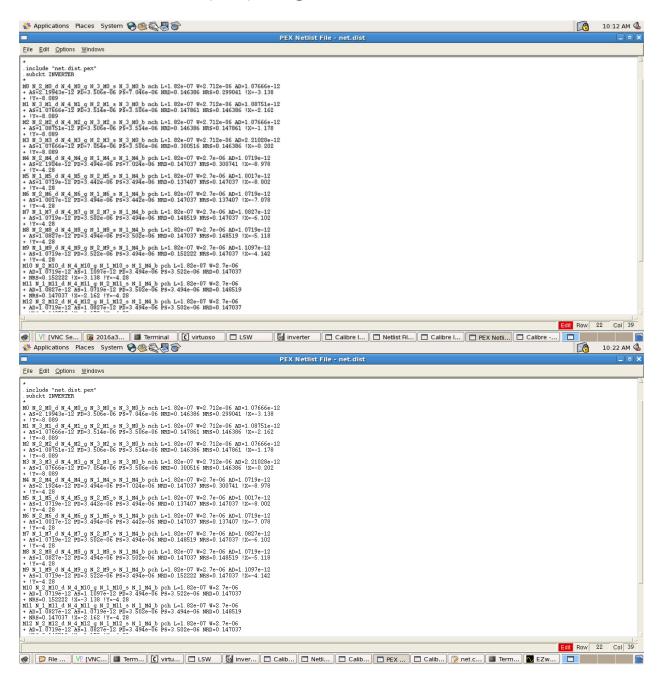
Fig 8: Schematic for LVS

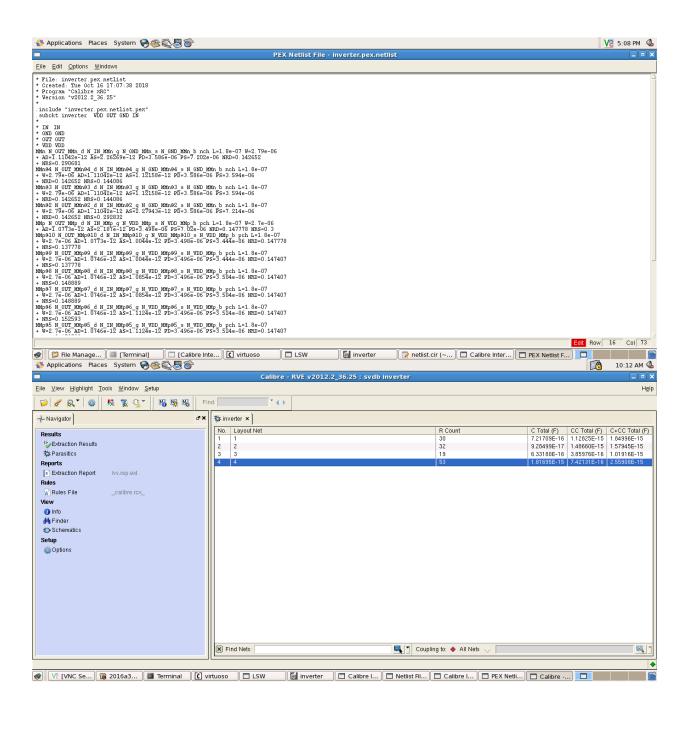
(CLoad was removed)

LVS was done successfully.

#### d. PEX extraction

## Parasitic Extraction (PEX) using Calibre





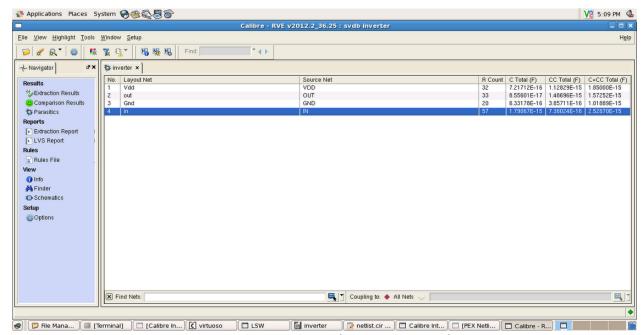


FIG 9: PEX Extraction (above 5 figures)

So, final output capacitance of was obtained as 1.57e-15 which is negligible compared to 1 pF CLoad i.e. 0.15% of the Load capacitance.

# 4. Schematic Circuit Simulations

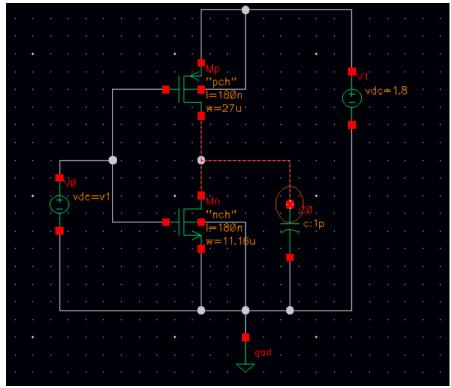


Fig 10: Schematic of the inverter

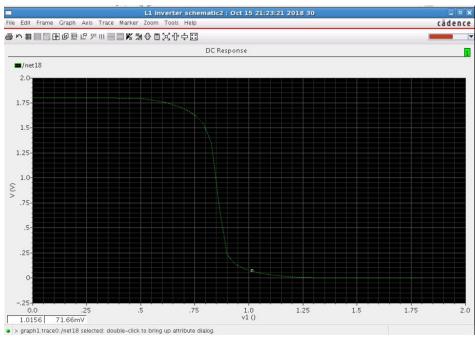


Fig 11: Voltage Transfer characteristics (VTC)

# a. Plot the energy and delay graph

#### **Delay graphs**

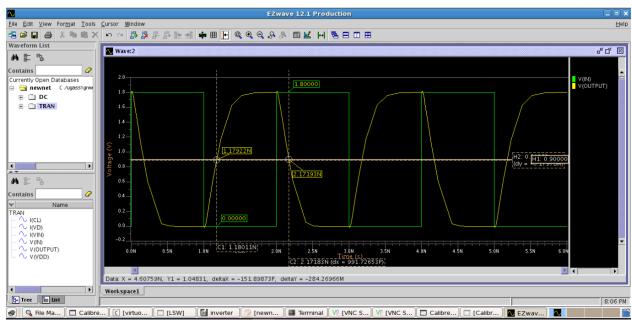
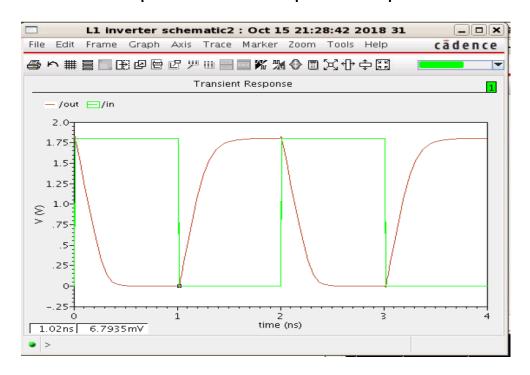


Fig 12: Delay Calculation using ELDO SPICE and Ezwave including PEX extracted parasitic capacitances and Load Capacitance of 1pF



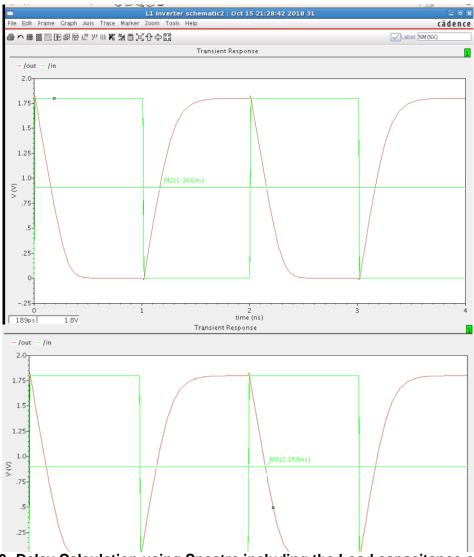


Fig 13: Delay Calculation using Spectre including the Load capacitance of 1pF

### **Energy Graph**

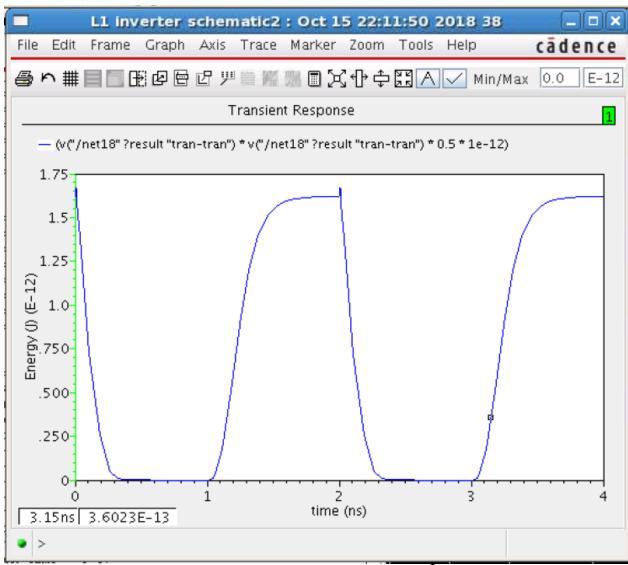


Fig 14: Energy =  $0.5 \times \text{Cout} \times \text{Vout}^2$ 

b. Plot the short circuit and switching power graph.

#### **Short Circuit Power Graph.**

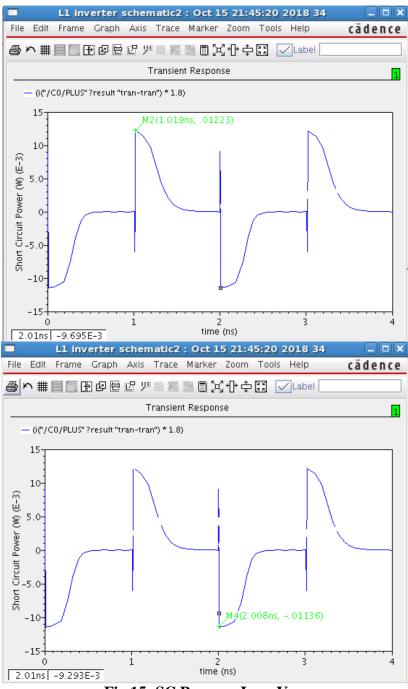


Fig 15: SC Power =  $I_{DS} \times V_{DD}$ 

#### **Switching or Dynamic Power Graph**

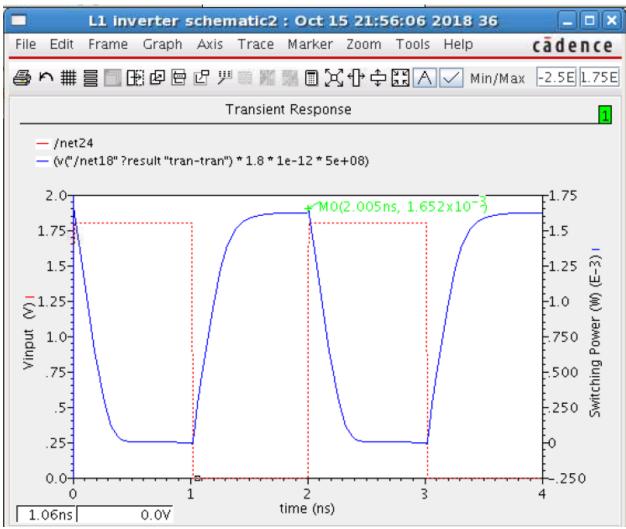


Fig 16: Switching power = (SP)  $\times V_{DD} \times V_{OUT} \times C_{LOAD} \times Frequency$ 

For inverter Switching probability = 1